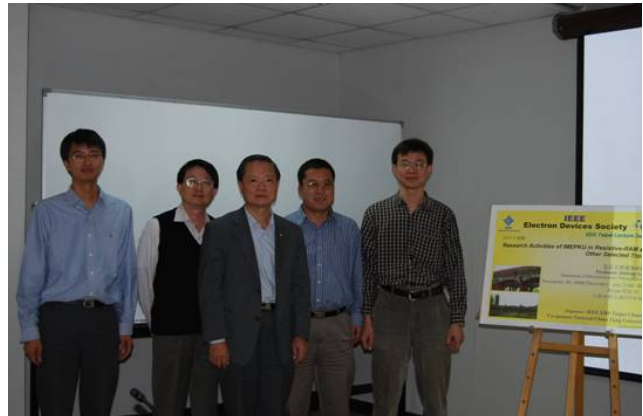


Resistance Random Access Memory, RRAM Prof. JingFeng Kang

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北京大學微電子所 Prof. Jing Feng Kang 受工研院邀請來新竹演講，主題為目前熱門的電阻式記憶體（Resistance Random Access Memory, RRAM），電子元件分會（ED Taipei Chapter）順便邀請他來交大訪問，順道參觀奈米實驗室。康教授畢業於大連理工大學，後加入北大任教。其研究群於年第一篇的 VLSI 論文來自其研究群的成果。此次 EDS Taipei Chapter 邀請他講解其在發展 RRAM 的經驗與大家分享。同時也介紹北大在各領域的研究現況。北京大學微電子所也頗富盛名，在此國際化益受重視的情況下，台灣的各大學加強與大陸重點大學的研究合作，是必然的趨勢。次演講約有三十位參加，有幾為教授參加，大部份為研究生。

Prof. JingFeng Kang of Peiking university was invited by ITRI to give a lecture in a nonvolatile memory technology workshop, in which he gave a topic on the recent development of Resistance Random Access Memory, RRAM. ED Taipei chapter then invited him to visit NCTU campus as well as lab tour of NDL facility. He graduated from Da-Lien university of science and technology. Upon graduation, he then joined Peiking University as a faculty member. The first VLSI paper contributed from mainland China was from his group in 2008. By taking this opportunity for his visit to Hsinchu area, he was invited to give a talk to audiences from university professor as well as students. He shared with all the audiences on his recent development of RRAM. The current research focus in Peiking university has also been introduced. With its reputation in microelectronics and under the globalization trend worldwide, it has been a necessary step towards the mutual visits and cooperation between both sides of the strait. Around 30 attendees, including 8 professors, and more than 20 graduate students, attended this talk.

